

## **Amendments to the Claims:**

This listing of claims will replace all previous versions of the claims:

1. (Original) A surface acoustic wave device comprising:  
a piezoelectric substrate; and  
an electrode section, disposed on the piezoelectric substrate, having a thin-film structure,  
wherein the electrode section includes interdigital electrodes and junction electrodes connected to the interdigital electrodes, and the interdigital electrodes each include corresponding first base layers containing Ta and Cu layers or Cu-M alloy layers each disposed on the corresponding first base layers, where M represents one or more elements selected from the group consisting of Ag, Sn, and C.
2. (Previously Presented) The surface acoustic wave device according to Claim 1, wherein the Cu layers or Cu-M alloy layers have a crystal structure in which crystals are oriented in a (111) direction.
3. (Original) The surface acoustic wave device according to Claim 2, wherein the Cu layers or Cu-M alloy layers have an average grain size ranging from 10 to 100 nm.
4. (Original) The surface acoustic wave device according to Claim 1, wherein the Cu layers or Cu-M alloy layers contain crystal grains having a face-centered cubic structure and the element M is precipitated at grain boundaries.
5. (Previously Presented) The surface acoustic wave device according to Claim 1, wherein the element M is Ag and an Ag content of the Cu-M alloy layers ranges from 0.5 to 10% by mass.
6. (Previously Presented) The surface acoustic wave device according to Claim 5, wherein the Ag content of the Cu-M alloy layers ranges from 0.8 to 10% by mass.
7. (Currently Amended) The surface acoustic wave device according to Claim 1, further comprising second base layers each disposed under the

corresponding first base layers, wherein the second base layers contain at least one of titanium ~~and~~ or a titanium oxides.

8. (Previously Presented) The surface acoustic wave device according to Claim 7, wherein the second base layers have a configuration in which the titanium oxides are disposed on a region containing only titanium and an oxygen content of the titanium oxides gradually increases from lower faces of the second base layers toward upper faces.

9. (Original) The surface acoustic wave device according to Claim 1, wherein the first base layers have a thickness ranging from 5 to 15 nm.

10. (Original) The surface acoustic wave device according to Claim 7, wherein the second base layers have a thickness ranging from 3 to 15 nm.

11. (Original) The surface acoustic wave device according to Claim 1, wherein the Cu layers or Cu-M alloy layers have a thickness ranging from 30 to 150 nm.

12. (Original) The surface acoustic wave device according to Claim 1, further comprising protective layers, each disposed on the corresponding Cu layers or Cu-M alloy layers, containing Cr.

13.-22. (Cancelled)